

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. Cancelled.

2. (Currently amended): A CMP polishing slurry used for polishing inorganic insulating film, comprising cerium oxide particles, an organic compound having an acetylene bond and water, [[,]]

wherein the organic compound having the acetylene bond is represented by the general formula (I):



wherein R^1 is a hydrogen atom or a substituted or unsubstituted alkyl group of 1 to 5 carbon atoms; and R^2 is a substituted or unsubstituted alkyl group of 4 to 10 carbon atoms.

3. Cancelled.

4. (Currently amended): The CMP polishing slurry according to claim 2 [[or 3]] which further contains a water-soluble high polymer compound comprising a polymer of a vinyl compound.

5. (Currently amended): A method for polishing a substrate, wherein the substrate on which a film to be polished is formed is pressed under pressure against a polishing cloth on a polishing platen, and the film on the substrate and the polishing cloth are relatively moved while the CMP polishing slurry according to any one of claim 2 [[or 3]] is supplied between the film and the polishing cloth, thereby polishing the film.

6. (Currently amended): A method for polishing a substrate, wherein the substrate on which a film to be polished is formed is pressed under pressure against a polishing cloth on a polishing platen, and the film on the substrate and the polishing cloth are relatively moved while a CMP polishing slurry comprising cerium oxide particles, an organic compound having an acetylene bond and water is supplied between the film and the polishing cloth and the acetylene bond segment of the organic compound is kept adsorbed on the film, thereby polishing the film, wherein the organic compound having the acetylene bond is represented by the general formula (I):



wherein R¹ is a hydrogen atom or a substituted or unsubstituted alkyl group of 1 to 5 carbon atoms; and R² is a substituted or unsubstituted alkyl group of 4 to 10 carbon atoms.

7. (Original): The method for polishing the substrate according to claim 6, wherein the CMP polishing slurry further contains a water-soluble high polymer compound comprising a polymer of a vinyl compound.

8. (Currently amended): A solution for a CMP polishing slurry, wherein the solution contains an organic compound having an acetylene bond represented by the general formula (I):



wherein [[R¹]] R¹ is a hydrogen atom or a substituted or unsubstituted alkyl group of 1 to 5 carbon atoms; and R² is a substituted or unsubstituted alkyl group of 4 to 10 carbon atoms.

9. Cancelled.